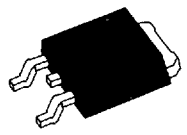
FEATURES

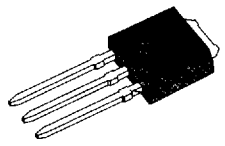
- Lower $R_{DS\ (ON)}$
- Improved inductive ruggedness
- Fast switching times
- Rugged polysilicon gate cell structure
- Lower input capacitance
- Extended safe operating area
- Improved high temperature reliability

D-PACK



IRFR010/012
IRFR014/015

I-PACK



IRFU010/012
IRFU014/015

PRODUCT SUMMARY

Part Number	V_{DS}	$R_{DS(on)}$	I_D
IRFR010/U010	50V	0 20Ω	8.2A
IRFR012/U012	50V	0 30Ω	6.7A
IRFR014/U014	60V	0 20Ω	8 2A
IRFR015/U015	60V	0.32Ω	6.7A

ABSOLUTE MAXIMUM RATINGS

Characteristic	Symbol	IRFR010 IRFU010	IRFR012 IRFU012	IRFR014 IRFU014	IRFR015 IRFU015	Unit
Drain-Source Voltage (1)	V_{DSS}	50		60		Vdc
Drain-Gate Voltage (R_{GS}=1 0MΩ)(1)	V_{DGR}	50		60		Vdc
Gate-Source Voltage	V_{GS}	±20				Vdc
Continuous Drain Current T_C=25°C	I_D	8.2	6.7	8.2	6.7	Adc
Continuous Drain Current T_C=100°C	I_D	5.2	4.2	5.2	4.2	Adc
Drain Current—Pulsed (3)	I_{DM}	33	27	33	27	Adc
Gate Current—Pulsed	I_{GM}	±1.5				Adc
Single Pulsed Avalanche Energy (4)	E_{AS}	1.4				mJ
Avalanche Current	I_{AS}	8 2				A
Total Power Dissipation at T_C=25°C Derate above 25°C	P_D	25 0.20				Watts W/°C
Operating and Storage Junction Temperature Range	T_J, Tstg	−55 to 150				°C
Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5 seconds	T_L	300				°C

Notes: (1) T_J=25°C to 150°C
(2) Pulse test Pulse width≤300μs, Duty Cycle≤2%
(3) Repetitive rating: Pulse with limited by max junction temperature
(4) L=50μH, V_{dd}=25V, R_G=25Ω, Starting T_J=25°C

ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise specified)

Symbol	Characteristic	Min	Typ	Max	Units	Test Conditions
BV_{DSS}	Drain-Source Breakdown Voltage IRFR014/015, IRFU014/015 IRFR010/012, IRFU010/012	 60 50	 — —	 — —	 V V	V_{GS}=0V, I_D=250μA
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	V_{DS}=V_{GS}, I_D=250μA
I_{GSS}	Gate-Source Leakage Forward	—	—	100	nA	V_{GS}=20V
I_{GSS}	Gate-Source Leakage Reverse	—	—	−100	nA	V_{GS}=−20V
I_{DSS}	Zero Gate Voltage Drain Current	— —	— —	250 1000	μA	V_{DS}=Max. Rating, V_{GS}=0V V_{DS}=0.8 Max Rating, V_{GS}=0V, T_J=125°C
$I_{D(on)}$	On-State Drain-Source Current (2) IRFR010/014, IRFU010/014 IRFR012/015, IRFU012/015	 8.2 6.7	 — —	 — —	 A	V_{DS}≥2.4V, V_{GS}=10V
$R_{DS(on)}$	Static Drain-Source IRFR010/014, IRFU010/014 IRFR012/015, IRFU012/015	 — —	 0.15 —	 0.20 0.30	 Ω	V_{GS}=10V, I_D=4.2A
g_{fs}	Forward Transconductance (2)	2.1	—	—	℧	V_{DS}≥50V, I_D=3.6A
C_{iss}	Input Capacitance	—	358	—	pF	V_{GS}=0V
C_{oss}	Output Capacitance	—	134	—	pF	V_{DS}=25V
C_{rss}	Reverse Transfer Capacitance	—	55	—	pF	f=1.0MHz
$t_{d(on)}$	Turn-On Delay Time	—	—	17	ns	V_{DD}=0.5 BV_{DSS}, I_D=7.3A, Z_O=24Ω (MOSFET switching times are essentially independent of operating temperature)
t_r	Rise Time	—	—	50	ns	
$t_{d(off)}$	Turn-Off Delay Time	—	—	18	ns	
t_f	Fall Time	—	—	35	ns	
Q_g	Total Gate Charge (Gate-Source Plus Gate-Drain)	—	—	10	nC	V_{GS}=10V, I_D=7.3A, V_{DS}=0 8Max. Rating (Gate charge is essentially independent of operating temperature.)
Q_{gs}	Gate-Source Charge	—	—	2.6	nC	
Q_{gd}	Gate-Drain ("Miller") Charge	—	—	4.8	nC	

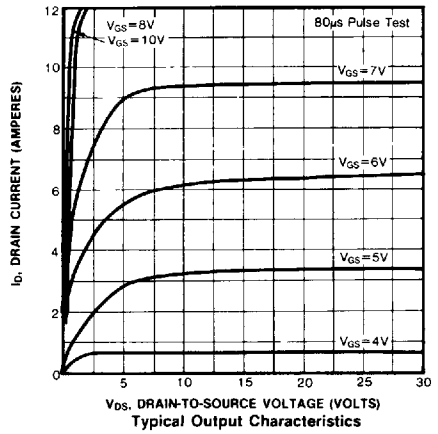
THERMAL RESISTANCE

R_{thJC}	Junction-to-Case	MAX	5.0	K/W	
R_{thCS}	Case-to-Sink	TYP	1.7	K/W	Mounting surface flat smooth, and greased
R_{thJA}	Junction-to-Ambient	MAX	110	K/W	Free Air Operation

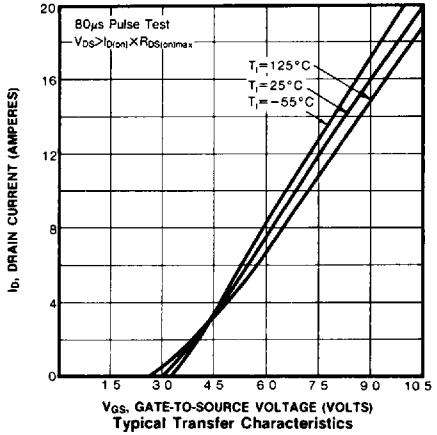
Notes: (1) T_J=25°C to 150°C
(2) Pulse test: Pulse width≤300μs, Duty Cycle≤2%
(3) Repetitive rating: Pulse width limited by max. junction temperature

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

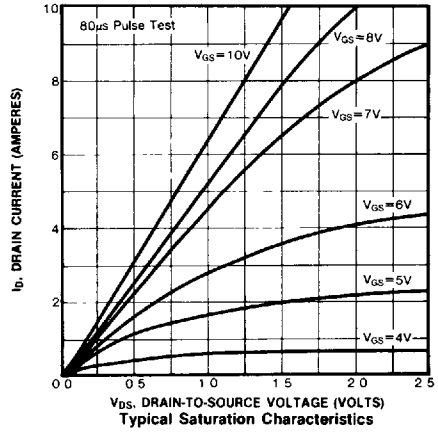
Symbol	Characteristic	Min	Typ	Max	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)					Modified MOSFET integral reverse
	IRFR010/014, IRFU010/014	—	—	8.2	A	P-N junction
	IRFR010/015, IRFU012/015	—	—	6.7	A	rectifier
I_{SM}	Pulse Source Current (3)					
	IRFR010/014, IRFU010/014	—	—	33	A	
	IRFR012/015, IRFU012/015	—	—	27	A	
V_{SD}	Diode Forward Voltage	—	—	1.6	V	T_C=25°C, I_S=8.2A, V_{GS}=0V
t_{rr}	Reverse Recovery Time	—	—	190	ns	T_j=25°C, I_F=7.3A, dI_F/dt=100A/μS



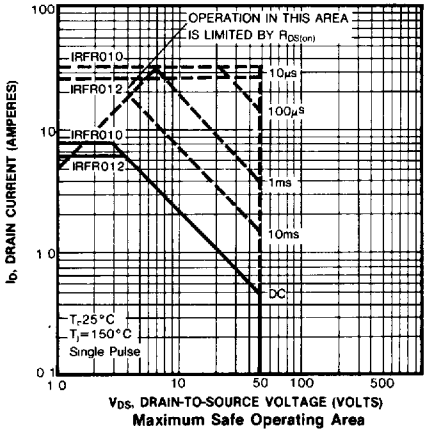
Typical Output Characteristics



Typical Transfer Characteristics



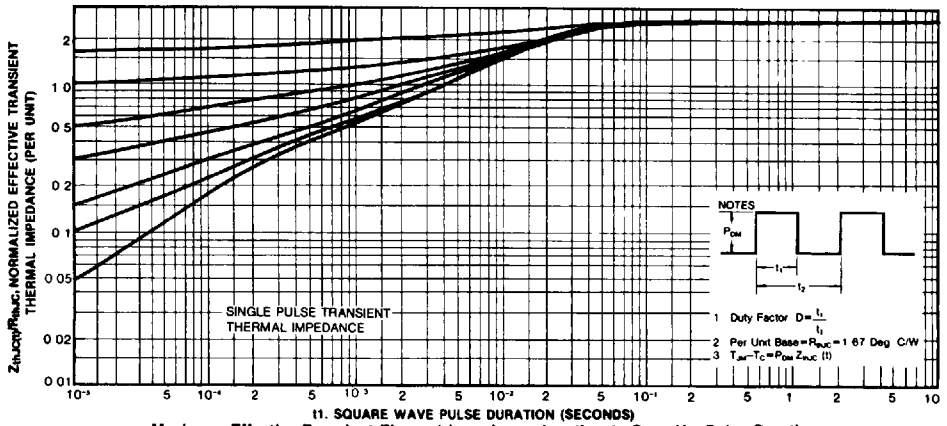
Typical Saturation Characteristics



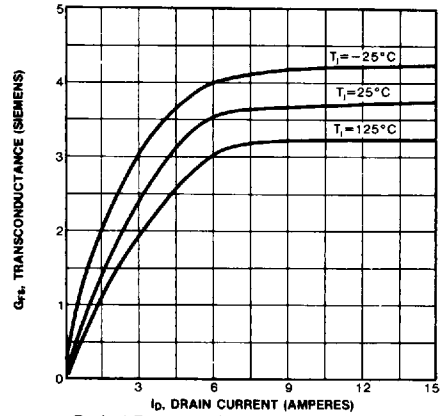
Maximum Safe Operating Area

Notes: (1) T_J=25°C to 150°C
(2) Pulse test. Pulse width≤300μs, Duty Cycle≤2%
(3) Repetitive rating: Pulse with limited by max. junction temperature

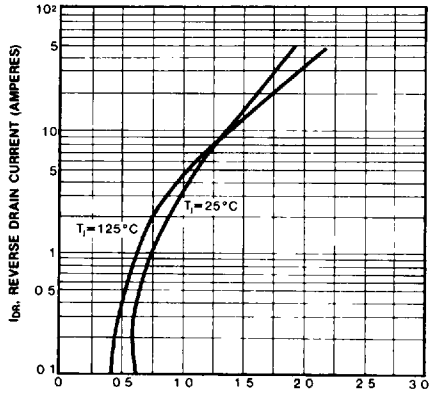
SAMSUNG ELECTRONICS



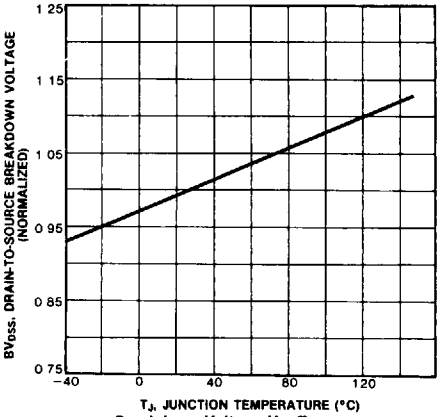
Maximum Effective Transient Thermal Impedance Junction-to-Case Vs. Pulse Duration



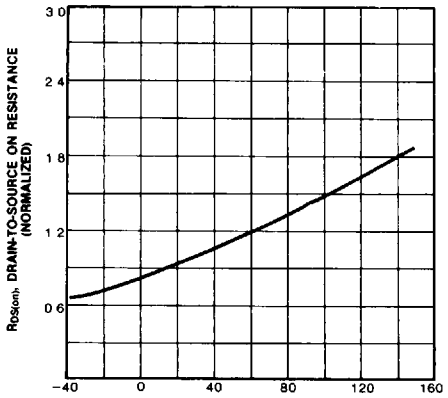
Typical Transcounductance Vs. Drain Current



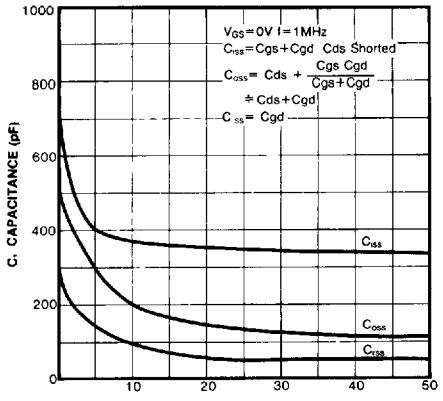
Typical Source—Drain Diode Forward Voltage



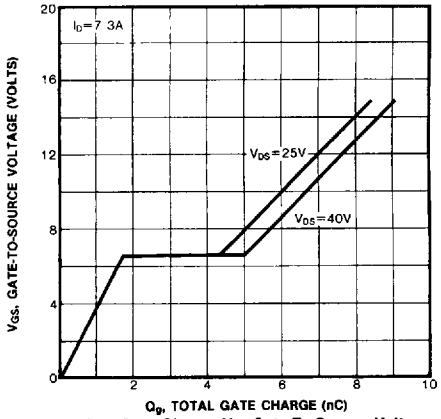
Breakdown Voltage Vs. Temperature



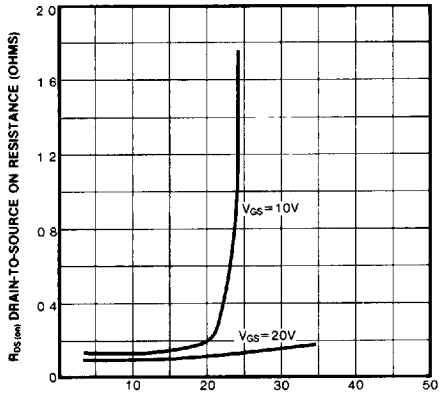
Normalized On-Resistance Vs. Temperature



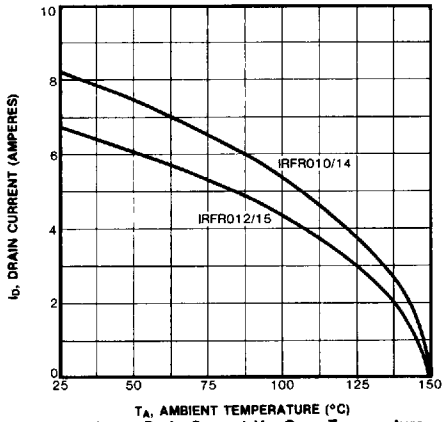
Typical Capacitance Vs. Drain to Source Voltage



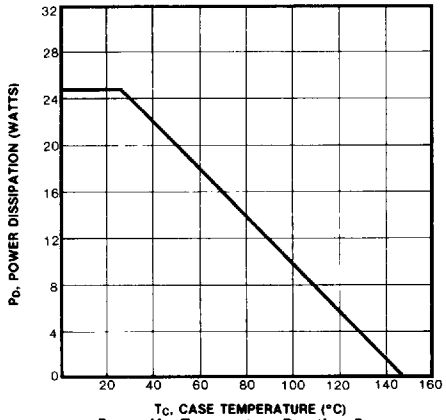
Typical Gate Charge Vs. Gate-To-Source Voltage



Typical On-Resistance Vs. Drain Current



Maximum Drain Current Vs. Case Temperature



Power Vs. Temperature Derating Curve